

# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

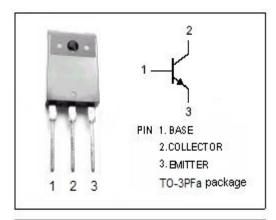
- · High Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 1300V (Min.)
- · High Switching Speed
- · Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

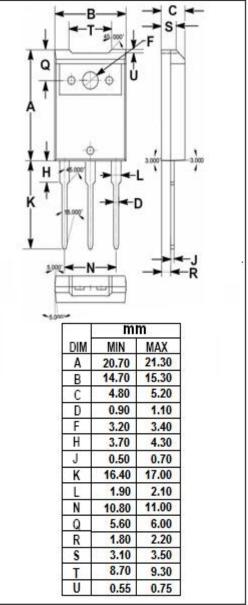
#### **APPLICATIONS**

• Designed for horizontal deflection output applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1300	V	
V <sub>CES</sub>	Collector- Emitter Voltage	1300	V	
Vceo	Collector-Emitter Voltage	700	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
Ic	Collector Current- Continuous	2	Α	
I <sub>CM</sub>	Collector Current-Peak	6	Α	
I <sub>BM</sub>	Base Current-Peak	2.5	Α	
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25℃	2.5		
	Collector Power Dissipation @ T <sub>C</sub> =25°C	80	VV	
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$ C	







### isc Silicon NPN Power Transistor

2SD1576

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

16-25 C uniess otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 1A			5.0	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 1A			1.5	V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 750V; I <sub>E</sub> = 0 V <sub>CB</sub> = 1300V; I <sub>E</sub> = 0			50 1.0	μA mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	2						
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V; f <sub>test</sub> = 0.5MHz		2		MHz			
Switching times									
t <sub>stg</sub>	Storage Time	L-25A L-11A.L-10			9.0	μς			
t <sub>f</sub>	Fall Time	- Ic= 2.5A , I <sub>B</sub> = 1.1A; L <sub>B</sub> = 10 μ H			1.0	μs			

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